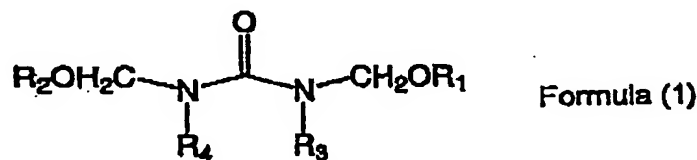


Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A composition for forming anti-reflective coating used for lithography process for manufacturing a semiconductor device characterized by containing a compound of formula (1), a condensation product thereof or a resin produced from the compound



wherein R₁ and R₂ are independently of each other hydrogen atom or an alkyl group, R₃ and R₄ are independently of each other hydrogen atom, methyl group, ethyl group, hydroxymethyl group or an alkoxymethyl ~~group~~, group, and an acid and/or acid generator, and the compound, the condensation product thereof or the resin produced from the compound is contained in an amount of 50 mass% or more in a solid content of the composition for forming anti-reflective coating.

2. (Canceled)

3. (Canceled)

4. (Previously Presented) The composition for forming anti-reflective coating according to claim 1, further containing a light absorbing compound and/or a light absorbing resin.

5. (Original) The composition for forming anti-reflective coating according to claim 4, wherein the light absorbing compound is at least one compound selected from naphthalene compounds and anthracene compounds.

6. (Original) The composition for forming anti-reflective coating according to claim 4, wherein the light absorbing compound is at least one compound selected from triazine compounds and triazine trione compounds.

7. (Original) The composition for forming anti-reflective coating according to claim 4, wherein the light absorbing resin is a resin having in the structure at least one aromatic ring structure selected from benzene ring, naphthalene ring and anthracene ring.

8. (Previously Presented) The composition for forming anti-reflective coating according to claim 1, further containing a resin having at least one crosslink-forming substituent selected from hydroxy group, carboxy group, amino group and thiol group.

9. (Canceled)

10. (Currently Amended) A method of forming an anti-reflective coating for use in a lithography process in a manufacture of a semiconductor device, characterized by comprising the steps of: coating the composition for forming anti-reflective coating according to claim 1 on a substrate, and baking it.

11. (Previously Presented) A process for manufacturing a semiconductor device, characterized by comprising the steps of:

coating the composition for forming anti-reflective coating according to claim 1 on a substrate and baking it to form an anti-reflective coating;

forming a photoresist on the anti-reflective coating;

exposing the substrate covered with the anti-reflective coating and the photoresist with a light;

developing it;

transferring an image on the substrate by etching to form an integrated circuit device.